

GaAs SPDT Terminated Switch DC - 3.0 GHz



Features

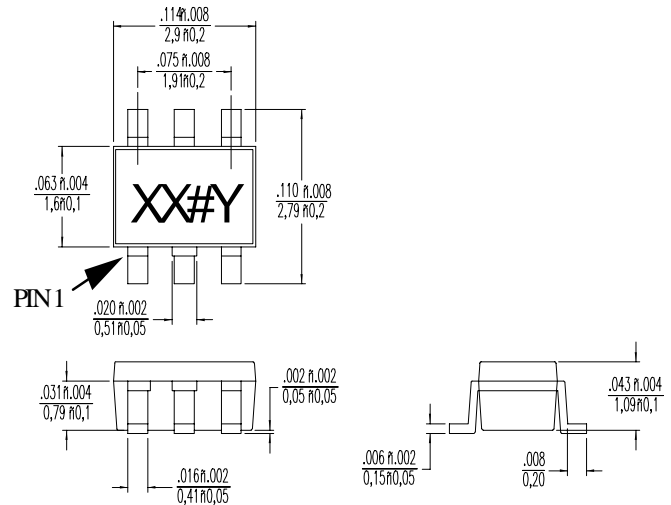
- Low Cost Plastic SOT-26 Package
- Low Insertion Loss <0.6 dB @ 900 MHz
- High Isolation >38 dB @ 900 MHz
- Low Power Consumption <10µA @ +3V
- Positive or Negative 2.5 to 8 V Control

Description

M/A-COM's SW-442 is a GaAs monolithic switch in a low cost SOT-26 surface mount plastic package. The SW-442 is ideally suited for applications where very low power consumption, low insertion loss, very small size and low cost are required. Typical application is in dual band systems where switching between small signal components is required such as filter banks, single band LNA's, converters etc. The SW-442 can be used in applications up to 0.25 Watts in systems such as CDMA, W-CDMA, PCS, DCS1800, GSM and other analog/digital wireless communications systems.

The SW-442 is fabricated using a mature 0.8 micron GaAs MESFET process. The process features full passivation for increased performance and reliability.

SOT-26 Plastic Package



Ordering Information

| Part Number | Package |
|-------------|------------------------------------|
| SW-442 PIN | SOT-26 Plastic Package |
| SW-442TR | Forward Tape and Reel ¹ |
| SW-442RTR | Reverse Tape and Reel ¹ |
| SW-442SMB | Sample Board |

1. Reference Application Note M513 for reel size information.

Electrical Specifications $T_A = 25^\circ\text{C}$

| Parameter | Test Conditions | Units | Min. | Typ. | Max. |
|-------------------------|---|-------|------|-------|-------|
| Insertion Loss | DC - 1 GHz | dB | | 0.5 | 0.7 |
| | 1 - 2 GHz | dB | | 0.8 | 1.0 |
| | 2 - 3 GHz | dB | | 1.1 | 1.25 |
| Isolation | DC - 1 GHz | dB | 36 | 38 | |
| | 1 - 2 GHz | dB | 25 | 28 | |
| | 2 - 3 GHz | dB | 21 | 22 | |
| VSWR | DC - 2 GHz | | | 1.4:1 | 1.5:1 |
| | 2 - 3 GHz | | | 1.6:1 | 1.7:1 |
| P_{1dB} (2.7V supply) | 500 MHz - 3 GHz | dBm | | 24 | |
| P_{1dB} (5V supply) | 500 MHz - 3 GHz | dBm | | 28 | |
| IP_2 (2.7V supply) | 2-Tone 900 MHz, 5 MHz spacing, 10 dBm each tone | dBm | | 80 | |
| IP_3 (2.7V supply) | 2-Tone 900 MHz, 5 MHz spacing, 10 dBm each tone | dBm | | 50 | |
| T_{rise} , T_{fall} | 10% to 90% RF, 90% to 10% RF | ns | | 40 | |
| | 50% Control to 90% RF, Control to 10% RF | ns | | 60 | |
| Transients | T_{on} , T_{off} | mV | | 10 | |
| | In-Band | | | | |
| Gate Leakage | $V_{CTL} = 2.5V$ | µA | | 6 | 15 |

Absolute Maximum Ratings¹

| Parameter | Absolute Maximum |
|-----------------------------|------------------|
| Input Power (0.5 - 3.0 GHz) | |
| 3V Control | +30 dBm |
| 5V Control | +33 dBm |
| Operating Voltage | +8.5 Volts |
| Operating Temperature | -40°C to +85°C |
| Storage Temperature | -65°C to +150°C |

1. Exceeding any one or combination of these limits may cause permanent damage.

Truth Table

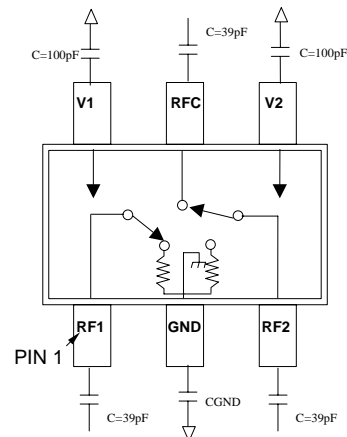
| Mode (Control) | V1 | V2 | RFC - RF1 | RFC - RF2 |
|-----------------------|--------------|--------------|-----------|-----------|
| Positive ¹ | 0±0.2V | +2.5 to +8V | On | Off |
| | +2.5 to +8V | 0±0.2V | Off | On |
| Negative ² | 0±0.2V | -2.5V to -8V | Off | On |
| | -2.5V to -8V | 0±0.2V | On | Off |

- External DC blocking capacitors are required on all RF ports and GND. GND capacitors can be used with positive control voltage to resonate lead inductance for improved isolation.
- If negative control is used, DC blocking capacitors and GND capacitors are not required.

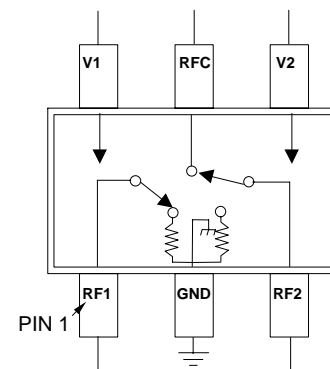
PIN Configuration

| PIN No. | Function | Description |
|---------|----------|-------------|
| 1 | RF1 | RF in/out |
| 2 | GND | RF Ground |
| 3 | RF2 | RF in/out |
| 4 | V2 | V Control 2 |
| 5 | RFC | RF COMMON |
| 6 | V1 | V Control 1 |

Functional Schematic Positive Control Voltage



Functional Schematic Negative Control Voltage



Handling Procedures

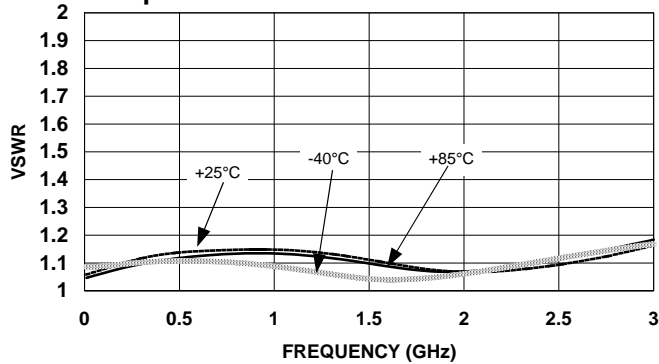
The following precautions should be observed to avoid damage:

Static Sensitivity

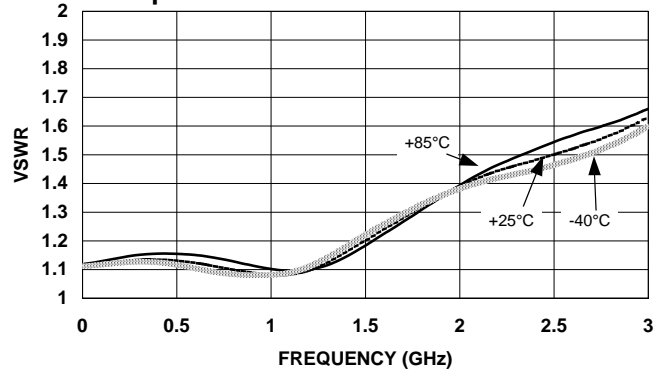
Gallium Arsenide Integrated Circuits are ESD sensitive and can be damaged by static electricity. Proper ESD techniques should be used when handling these devices.

Typical Performance Curves

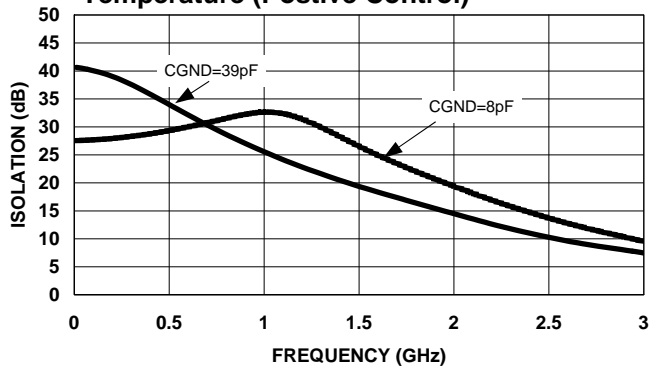
Output VSWR vs. Frequency over Temperature



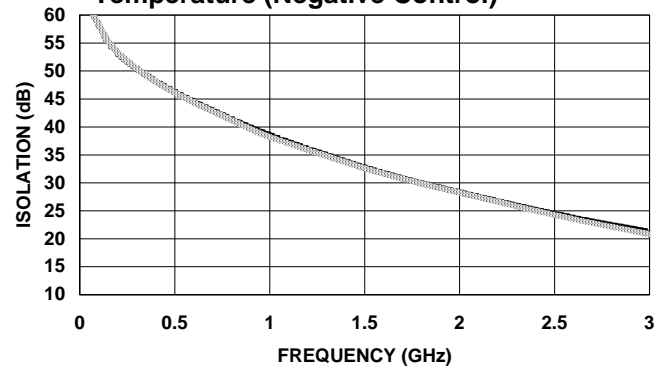
Input VSWR vs. Frequency over Temperature



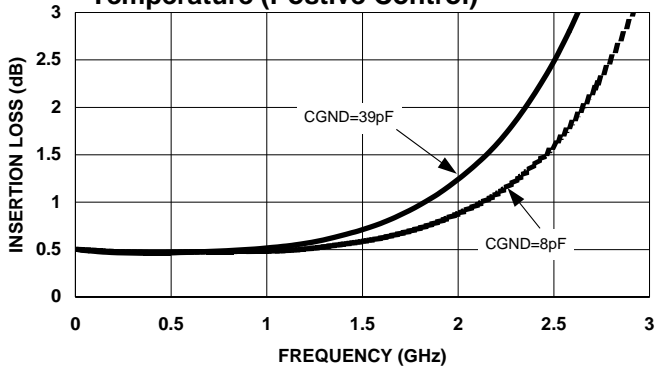
Isolation Loss vs. Frequency over Temperature (Positive Control)



Isolation Loss vs. Frequency over Temperature (Negative Control)



Insertion Loss vs. Frequency over Temperature (Positive Control)



Insertion Loss vs. Frequency over Temperature (Negative Control)

